Amplifier Transistors

NPN Silicon

Features

• These are Pb-Free Devices*



Rating	Symbol	Value	Unit
Collector – Emitter Voltage	V _{CEO}	50	Vdc
Collector - Base Voltage	V _{CBO}	60	Vdc
Emitter-Base Voltage	V _{EBO}	6.0	Vdc
Collector Current – Continuous	I _C	100	mAdc
Total Device Dissipation @ T _A = 25°C Derate above 25°C	P _D	350 2.8	mW mW/°C
Total Device Dissipation @ T _C = 25°C Derate above 25°C	P _D	1.0 8.0	W mW/°C
Operating and Storage Junction Temperature Range	T _J , T _{stg}	-55 to +150	°C

THERMAL CHARACTERISTICS

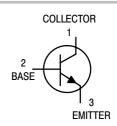
Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	357	°C/W
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	125	°C/W

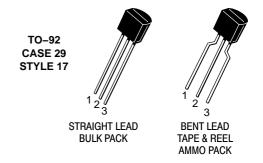
Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.



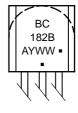
ON Semiconductor®

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MARKING DIAGRAM



A = Assembly Location

Y = Year WW = Work Week = Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

Device	Package	Shipping [†]
BC182G	TO-92 (Pb-Free)	5000 Units / Bulk
BC182BG	TO-92 (Pb-Free)	5000 Units / Bulk
BC182BRL1G	TO-92 (Pb-Free)	2000 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

^{*}For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

ELECTRICAL CHARACTERISTICS ($T_A = 25^{\circ}C$ unless otherwise noted)

Characteristic		Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS				•	•	
Collector – Emitter Breakdown Voltage $(I_C = 2.0 \text{ mA}, I_B = 0)$		V _{(BR)CEO}	50	_	_	V
Collector – Base Breakdown Voltage ($I_C = 10 \mu A, I_E = 0$)		V _{(BR)CBO}	60	-	_	V
Emitter – Base Breakdown Voltage ($I_E = 100 \mu A$, $I_C = 0$)		V _{(BR)EBO}	6.0	-	_	V
Collector Cutoff Current (V _{CB} = 50 V, V _{BE} = 0)		I _{CBO}	_	0.2	15	nA
Emitter–Base Leakage Current (V _{EB} = 4.0 V, I _C = 0)		I _{EBO}	_	-	15	nA
ON CHARACTERISTICS						
DC Current Gain (I _C = 10 μ A, V _{CE} = 5.0 V)	BC182	h _{FE}	40	_	-	_
$(I_C = 2.0 \text{ mA}, V_{CE} = 5.0 \text{ V})$	BC182 BC182B		120 180	_ _	500 500	
$(I_C = 100 \text{ mA}, V_{CE} = 5.0 \text{ V})$	BC182		80	-	_	
Collector – Emitter On Voltage ($I_C = 10 \text{ mA}$, $I_B = 0.5 \text{ mA}$) ($I_C = 100 \text{ mA}$, $I_B = 5.0 \text{ mA}$) (Note 1)		V _{CE(sat)}	_ _	0.07 0.2	0.25 0.6	V
Base – Emitter Saturation Voltage (I _C = 100 mA, I _B = 5.0 mA) (Note 1)		V _{BE(sat)}	_	-	1.2	V
Base–Emitter On Voltage ($I_C = 100 \mu A, V_{CE} = 5.0 V$) ($I_C = 2.0 mA, V_{CE} = 5.0 V$) ($I_C = 100 mA, V_{CE} = 5.0 V$) (Note 1)		V _{BE(on)}	- 0.55 -	0.5 0.62 0.83	- 0.7 -	V
DYNAMIC CHARACTERISTICS						
Current – Gain — Bandwidth Product ($I_C = 0.5$ mA, $V_{CE} = 3.0$ V, $f = 100$ MHz) ($I_C = 10$ mA, $V_{CE} = 5.0$ V, $f = 100$ MHz)		f _T	_ 150	100 200		MHz
Common Base Output Capacitance (V _{CB} = 10 V, I _C = 0, f = 1.0 MHz)		$C_{\sf ob}$	_	-	5.0	pF
Common Base Input Capacitance (V _{EB} = 0.5 V, I _C = 0, f = 1.0 MHz)		C _{ib}	_	8.0	_	pF
Small–Signal Current Gain ($I_C = 2.0 \text{ mA}, V_{CE} = 5.0 \text{ V}, f = 1.0 \text{ kHz}$)	BC182 BC182B	h _{fe}	125 240	- -	500 500	-
Noise Figure (I _C = 0.2 mA, V _{CE} = 5.0 V, R _S = 2.0 k Ω , f = 1.0 kHz)		NF	_	2.0	10	dB

^{1.} Pulse Test: Tp 300 s, Duty Cycle 2.0%.

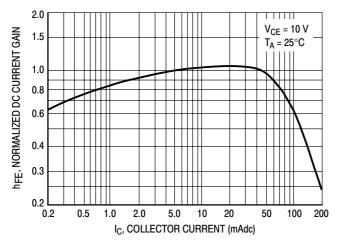


Figure 1. Normalized DC Current Gain

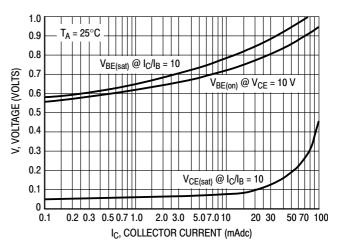


Figure 1. "Saturation" and "On" Voltages

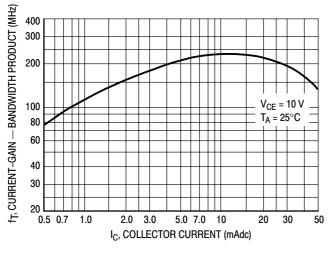


Figure 2. Current-Gain — Bandwidth Product

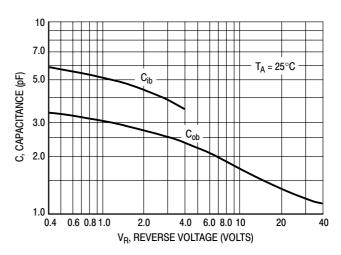


Figure 3. Capacitances

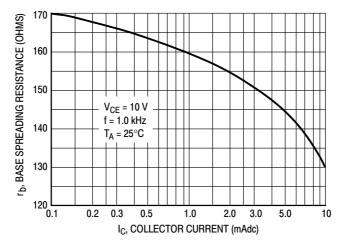
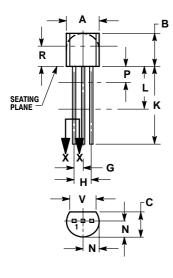


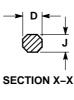
Figure 4. Base Spreading Resistance

PACKAGE DIMENSIONS

TO-92 (TO-226) CASE 29-11 **ISSUE AM**



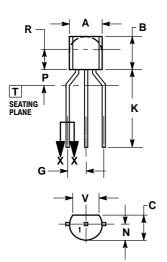
STRAIGHT LEAD **BULK PACK**



NOTES:

- 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982. CONTROLLING DIMENSION: INCH.
- CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED
- LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

	INCHES		MILLIN	IETERS
DIM	MIN	MAX	MIN	MAX
Α	0.175	0.205	4.45	5.20
В	0.170	0.210	4.32	5.33
C	0.125	0.165	3.18	4.19
D	0.016	0.021	0.407	0.533
G	0.045	0.055	1.15	1.39
Н	0.095	0.105	2.42	2.66
7	0.015	0.020	0.39	0.50
K	0.500		12.70	
L	0.250		6.35	
N	0.080	0.105	2.04	2.66
P		0.100		2.54
R	0.115		2.93	
٧	0.135		3.43	



BENT LEAD TAPE & REEL AMMO PACK



NOTES:

- DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
- CONTROLLING DIMENSION: MILLIMETERS.
 CONTOUR OF PACKAGE BEYOND
- DIMENSION R IS UNCONTROLLED
- LEAD DIMENSION IS UNCONTROLLED IN PAND BEYOND DIMENSION K MINIMUM.

	MILLIMETERS		
DIM	MIN	MAX	
Α	4.45	5.20	
В	4.32	5.33	
С	3.18	4.19	
D	0.40	0.54	
G	2.40	2.80	
J	0.39	0.50	
K	12.70		
N	2.04	2.66	
Р	1.50	4.00	
R	2.93		
٧	3.43		

STYLE 17:

COLLECTOR PIN 1.

BASE

EMITTER

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